Mikhail Dorokhin

List of Publications by Year
in descending order

103	516	933447 10	839539 18
papers	citations	h-index	g-index

104	104	104	290
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Using laser sputtering to obtain semiconductor nanoheterostructures. Journal of Optical Technology (A Translation of Opticheskii Zhurnal), 2008, 75, 389.	0.4	48
2	Ferromagnetic effect of a Mn delta layer in the GaAs barrier on the spin polarization of carriers in an InGaAs/GaAs quantum well. JETP Letters, 2010, 90, 658-662.	1.4	44
3	Emission properties of InGaAs/GaAs heterostructures with Î´âŸ¨MnâŸ©-doped barrier. Journal Physics D: Applied Physics, 2008, 41, 245110.	2.8	36
4	High-temperature intrinsic ferromagnetism in the (In,Fe)Sb semiconductor. Journal of Applied Physics, 2017, 122, .	2.5	25
5	Ferromagnetism in GaAs structures with Mn-delta-doped layers. Technical Physics Letters, 2009, 35, 643-646.	0.7	20
6	Electrical spin injection in forward biased Schottky diodes based on InGaAsâ€“GaAs quantum well heterostructures. Applied Physics Letters, 2006, 89, 181118.	3.3	19
7	Formation of a Domain Structure in Multilayer CoPt Films by Magnetic Probe of an Atomic Force Microscope. Physics of the Solid State, 2018, 60, 2200-2206.	0.6	18
8	CoPt ferromagnetic injector in light-emitting Schottky diodes based on InGaAs/GaAs nanostructures. Semiconductors, 2015, 49, 1601-1604.	0.5	14
9	Properties of CoPt ferromagnetic layers for application in spin light-emitting diodes. Physics of the Solid State, 2016, 58, 2267-2270.	0.6	14
10	Thermoelectric properties of low-cost transparent single wall carbon nanotube thin films obtained by vacuum filtration. Physica E: Low-Dimensional Systems and Nanostructures, 2019, 114, 113619.	2.7	14
11	Influence of deltaâŒ©MnâŒª doping parameters of the GaAs barrier on circularly polarized luminescence of GaAs/InGaAs heterostructures. Physics of the Solid State, 2010, 52, 2291-2296.	0.6	10
12	Application of cobalt in spin light-emitting Schottky diodes with InGaAs/GaAs quantum wells. Journal of Surface Investigation, 2015, 9, 706-709.	0.5	9
13	Photoluminescence response of a quantum well to a change in the magnetic field of the Mn Î´ Layer in InGaAs/GaAs heterostructures. Journal of Experimental and Theoretical Physics, 2011, 113, 138-147.	0.9	8
14	Magneto-Optical and Micromagnetic Properties of Ferromagnet/Heavy Metal Thin Film Structures. International Journal of Nanoscience, 2019, 18, 1940019.	0.7	8
15	Effect of an Interfacial Oxide Layer on the Electroluminescence Efficiency of Metalâ€“Quantum-Confined Semiconductor Heterostructures. Semiconductors, 2005, 39, 17.	0.5	7
16	Structural and optical properties of GaAsSb QW heterostructures grown by laser deposition. Semiconductors, 2015, 49, 109-112.	0.5	7
17	The circular polarization inversion in Î´âŸ¨MnâŸ©/InGaAs/GaAs light-emitting diodes. Applied Physics Letters, 2015, 107, 042406.	3.3	7
18	Optically controlled spin-polarization memory effect on Mn delta-doped heterostructures. Scientific Reports, 2016, 6, 24537.	3.3	7

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19	Modification of Magnetic Properties of a CoPt Alloy by Ion Irradiation. Physics of the Solid State, 2019, 61, 1646-1651.	0.6	7
20	The nature of transport and ferromagnetic properties of the GaAs structures with the Mn Î´-doped layer. Journal of Magnetism and Magnetic Materials, 2019, 478, 84-90.	2.3	7
21	Effect of Ion Irradiation on the Magnetic Properties of CoPt Films. Physics of the Solid State, 2021, 63, 386-394.	0.6	7
22	High-temperature intrinsic ferromagnetism in heavily Fe-doped GaAs layers. Semiconductor Science and Technology, 2020, 35, 125032.	2.0	7
23	Injection electroluminescence from quantum-size InGaAs/GaAs structures with metal/semiconductor and metal-oxide-semiconductor junctions. Journal of Surface Investigation, 2010, 4, 390-394.	0.5	6
24	Effects of a nearby Mn delta layer on the optical properties of an InGaAs/GaAs quantum well. Journal of Applied Physics, 2014, 116, 203501.	2.5	6
25	GaAs diodes for TiT2-based betavoltaic cells. Applied Radiation and Isotopes, 2022, 179, 110030.	1.5	6
26	LEDs based on InGaAs/GaAs heterostructures with magnetically controlled electroluminescence. Technical Physics Letters, 2011, 37, 1168-1171.	0.7	5
27	Photoconductive detector of circularly polarized radiation based on a MIS structure with a CoPt layer. Physics of the Solid State, 2017, 59, 2223-2225.	0.6	5
28	Specific Features of the Electrochemical Capacitanceâ€“Voltage Profiling of GaAs LED and pHEMT Structures with Quantum-Confined Regions. Semiconductors, 2018, 52, 1004-1011.	0.5	5
29	Micromagnetic and Magnetooptical Properties of Ferromagnetic/Heavy Metal Thin Film Structures. Physics of the Solid State, 2019, 61, 1577-1582.	0.6	5
30	Thermoelectrical properties of ternary lead chalcogenide plumbum-selenium-tellurium thin films with excess of tellurium prepared by plasma-chemical vapor deposition. Thin Solid Films, 2022, , 139244.	1.8	5
31	FORMATION OF MAGNETIC GaAs:Mn LAYERS FOR InGaAs/GaAs LIGHT EMITTING QUANTUM-SIZE STRUCTURES. International Journal of Nanoscience, 2007, 06, 221-224.	0.7	4
32	The effect of the Mn delta layer on the photosensitivity spectra of structures with In x Ga1 â^' x As/GaAs quantum wells. Journal of Surface Investigation, 2011, 5, 563-565.	0.5	4
33	GaMnSb/InGaAs/GaAs heterostructure leds with a ferromagnetic injector layer. Semiconductors, 2012, 46, 1518-1523.	0.5	4
34	Formation of spin light-emitting diodes based on InGaAs/GaAs heterostructures containing ferromagnetic inclusions. Bulletin of the Russian Academy of Sciences: Physics, 2012, 76, 225-228.	0.6	4
35	Chemical and phase composition of GaMnAs/GaAs/InGaAs spin light-emitting diodes. Semiconductors, 2014, 48, 815-820.	0.5	4
36	Tunneling and injection in ferromagnetic structures InGaAs/GaAs/(Ga,Mn)As and InGaAs/n +-GaAs/(Ga,Mn)As. Physics of the Solid State, 2016, 58, 2271-2276.	0.6	4

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37	Methods for spin injection managing in inGaAs/GaAs/Al2O3/CoPt spin light-emitting diodes. Physics of the Solid State, 2017, 59, 2155-2161.	0.6	4
38	Thermoelectric effects in nanoscale layers of manganese silicide. Semiconductors, 2017, 51, 1403-1408.	0.5	4
39	Heterostructures with InGaAs/GaAs quantum dots doped with transition elements: II. Study of the circularly polarized luminescence. Technical Physics, 2017, 62, 1545-1550.	0.7	4
40	Production of Si- and Ge-Based Thermoelectric Materials by Spark Plasma Sintering. Semiconductors, 2018, 52, 1559-1563.	0.5	4
41	In-situ Doping of Thermoelectric Materials Based on SiGe Solid Solutions during Their Synthesis by the Spark Plasma Sintering Technique. Semiconductors, 2019, 53, 1158-1163.	0.5	4
42	Acceleration of the precession frequency for optically-oriented electron spins in ferromagnetic/semiconductor hybrids. Scientific Reports, 2019, 9, 7294.	3.3	4
43	Molecular dynamics studies on spark plasma sintering of Geâ€“Si based thermoelectric material. AIP Advances, 2020, 10, .	1.3	4
44	Experimental Study of the Thermal Conductivity of Single-Walled Carbon Nanotube-Based Thin Films. Physics of the Solid State, 2020, 62, 1090-1094.	0.6	4
45	Circularly polarized electroluminescence of quantum-size InGaAs/GaAs heterostructures with ferromagnetic metal-GaAs Schottky contacts. Technical Physics Letters, 2006, 32, 1064-1066.	0.7	3
46	Properties of MnSb/GaAs heterostructures. Bulletin of the Russian Academy of Sciences: Physics, 2013, 77, 69-71.	0.6	3
47	Epitaxial growth of MnGa/GaAs layers for diodes with spin injection. Physics of the Solid State, 2014, 56, 2131-2134.	0.6	3
48	Dislocation gliding and cross-hatch morphology formation in AIII-BV epitaxial heterostructures. Applied Physics Letters, 2014, 105, 231608.	3.3	3
49	The effect of ferromagnetic Mn-delta-doped layer on the emission properties of GaAsSb/GaAs and InGaAs/GaAsSb/GaAs heterostructures. Technical Physics Letters, 2014, 40, 930-933.	0.7	3
50	Circularly polarized electroluminescence of light-emitting InGaAs/GaAs (III, Mn)V diodes on the basis of structures with a tunneling barrier. Semiconductors, 2015, 49, 1448-1452.	0.5	3
51	Temperature stabilization of spin-LEDs with a CoPt injector. Journal of Physics: Conference Series, 2017, 816, 012034.	0.4	3
52	Enhancing the Circular Polarization of Spin Light-Emitting Diodes by Processing in Selenium Vapor. Technical Physics Letters, 2019, 45, 235-238.	0.7	3
53	Studying Magnetic Diodes with a GaMnAs Layer Formed by Pulsed Laser Deposition. Semiconductors, 2019, 53, 332-338.	0.5	3
54	Ultra-high phosphorus-doped epitaxial Ge layers grown by HWCVD method on Si substrates. Materials Science in Semiconductor Processing, 2019, 100, 175-178.	4.0	3

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55	Simulation of the Parameters of a Titanium-Tritide-Based Beta-Voltaic Cell. Semiconductors, 2019, 53, 96-98.	0.5	3
56	Features of the formation of Mn doped InAs/GaAs quantum dots by vapor phase epitaxy. Journal of Surface Investigation, 2012, 6, 511-514.	0.5	2
57	Spin injection of electrons in GaMnAs/GaAs/InGaAs light-emitting diode structures with a tunnel junction. Technical Physics, 2014, 59, 1839-1843.	0.7	2
58	Structural perfection and the distribution of impurities in magnetic semiconductor nanoheterosystems based on GaAs. Bulletin of the Russian Academy of Sciences: Physics, 2014, 78, 6-8.	0.6	2
59	Effect of the dopant concentration on the luminescence properties of InGaAs/GaAs spin light-emitting diodes with a mn Î´ layer. Semiconductors, 2016, 50, 1-7.	0.5	2
60	Coherent spin dynamics of carriers in ferromagnetic semiconductor heterostructures with an Mn Î´ layer. Journal of Experimental and Theoretical Physics, 2016, 123, 420-428.	0.9	2
61	Emitting heterostructures with a bilayer InGaAs/GaAsSb/GaAs quantum well and a GaMnAs ferromagnetic layer. Physics of the Solid State, 2017, 59, 2216-2219.	0.6	2
62	Anomalous Nernst-Ettingshausen effect in Î´<Mn>GaAs/InGaAs ferromagnetic semiconductor heterostructures. Journal of Physics: Conference Series, 2018, 993, 012015.	0.4	2
63	Structural investigation of light-emitting A3B5 structures grown on Ge/Si(100) substrate. Journal of Physics: Conference Series, 2018, 1124, 022037.	0.4	2
64	Structural and optical characteristics of GaAs films grown on Si/Ge substrates. Journal of Physics: Conference Series, 2018, 993, 012014.	0.4	2
65	Structure, microhardness and thermal conducting properties of the high-pressure high-temperature-treated Alâ€“Tiâ€“N materials. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	2.3	2
66	New functional material: spark plasma sintered Si/SiO‹sub›2‹/sub› nanoparticles â€“ fabrication and properties. RSC Advances, 2019, 9, 16746-16753.	3.6	2
67	Studies of Thermoelectric Properties of Superlattices Based on Manganese Silicide and Germanium. Physics of the Solid State, 2019, 61, 2348-2352.	0.6	2
68	Electrical spinâ€injection and depolarization mechanisms in forward biased ferromagnetic Schottky diodes. Physica Status Solidi (B): Basic Research, 2009, 246, 1132-1137.	1.5	1
69	Electroluminescence of InGaAs/GaAs quantum-size heterostructures with (III, Mn)V and Ni ferromagnetic injectors. Semiconductors, 2010, 44, 1398-1401.	0.5	1
70	Temperature stability of photoluminescence in heterostructures with InGaAs/GaAs quantum well and Mn-delta-doped acceptor layer in GaAs barrier. Technical Physics Letters, 2010, 36, 819-822.	0.7	1
71	Electroluminescence And Spin-Polarized Hole Injection In InAsâ•GaAs Quantum Dot Heterostructures. , 2010, , .		1
72	Spin-polarized light-emitting diodes based on heterostructures with a GaAs/InGaAs/GaAs quantum well and ferromagnetic GaMnSb injection layer. Technical Physics Letters, 2012, 38, 764-767.	0.7	1

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73	Optical and magnetotransport properties of InGaAs/GaAsSb/GaAs structures doped with a magnetic impurity. Semiconductors, 2015, 49, 1430-1434.	0.5	1
74	On the crystal structure and thermoelectric properties of thin Si1â€“x Mn x films. Semiconductors, 2016, 50, 1453-1457.	0.5	1
75	Control of circular polarization of electroluminescence in spin light-emitting diodes based on InGaAs/GaAs/Î´âŒ©MnâŒª heterostructures. Physics of the Solid State, 2017, 59, 2162-2167.	0.6	1
76	Features of the selective manganese doping of GaAs structures. Semiconductors, 2017, 51, 1415-1419.	0.5	1
77	Heterostructures with InGaAs/GaAs quantum dots doped by transition elements. Part I: Photoluminescence properties. Technical Physics, 2017, 62, 1398-1402.	0.7	1
78	Raising the Operating Temperature of (Ga,Mn)As/GaAs Spin Light Emitting Diodes by Applying Post-Growth Treatment. Physics of the Solid State, 2018, 60, 2182-2187.	0.6	1
79	Detectors of Circularly Polarized Radiation Based on Semiconductor Heterostructures with a CoPt Schottky Barrier. Physics of the Solid State, 2018, 60, 2276-2279.	0.6	1
80	Diode Structures Based on (In, Fe)Sb/GaAs Magnetic Heterojunctions. Technical Physics Letters, 2019, 45, 668-671.	0.7	1
81	Study of Extended Electrically Active Defects in Heterostructures Based on (Ga,Mn)As/(In,Ga)As by Electron Beam-Induced Current and Deep-Level Transient Spectroscopy. Journal of Surface Investigation, 2019, 13, 105-110.	0.5	1
82	Long-Range Magnetic Interaction in InGaAs/GaAs/Î´-âŒ©MnâŒª Heterostructures. Technical Physics Letters, 2020, 46, 87-90.	0.7	1
83	Circularly Polarized Electroluminescence of Spin LEDs with a Ferromagnetic (In, Fe)Sb Injector. Technical Physics Letters, 2020, 46, 691-694.	0.7	1
84	Diode Heterostructures with a Ferromagnetic (Ga,Mn)As Layer. Physics of the Solid State, 2020, 62, 423-430.	0.6	1
85	Light-emitting properties of GaAs/InGaAs quantum wells with a GaAs barrier Î´-doped with Mn atoms. Bulletin of the Russian Academy of Sciences: Physics, 2009, 73, 11-14.	0.6	0
86	Magneto-optics Of Ferromagnetic InGaAsâˆ•GaAsâˆ•Î´-âŒ©MnâŒª Heterostructures. , 2011, , .		0
87	A magnetically controlled LED with S-shaped current-voltage characteristic. Technical Physics Letters, 2012, 38, 1045-1047.	0.7	0
88	Temperature dependence of the circular polarization of electroluminescence from spin-polarized light-emitting diodes based on InGaAs/GaAs heterostructures. Journal of Surface Investigation, 2014, 8, 433-439.	0.5	0
89	Fabrication of MnGa/GaAs contacts for optoelectronics and spintronics applications. Semiconductors, 2016, 50, 1443-1448.	0.5	0
90	Room temperature spin injection in a light-emitting diode based on a GaMnSb/n-GaAs/InGaAs tunnel junction. Journal of Physics: Conference Series, 2017, 816, 012035.	0.4	0

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91	Enhanced Photoluminescence of Heavily Doped n-Ge/Si(001) Layers. Semiconductors, 2019, 53, 1262-1265.	0.5	0
92	Formation of Carbon Layers by the Thermal Decomposition of Carbon Tetrachloride in a Reactor for MOCVD Epitaxy. Semiconductors, 2020, 54, 956-960.	0.5	0
93	Time-Resolved Photoluminescence in Heterostructures with InGaAs:Cr/GaAs Quantum Wells. Semiconductors, 2020, 54, 1341-1346.	0.5	0
94	Switching of magnetoresistive light-emitting diode by external magnetic field. Applied Physics Letters, 2021, 118, 092402.	3.3	0
95	The Thermoelectric Properties of Nanostructured SiGe Phosphorus Doped by Spark Plasma Sintering. , 2021, , .		0
96	Role of resident electrons in the manifestation of a spin polarization memory effect in Mn delta-doped GaAs heterostructures. Physical Review B, 2021, 104, .	3.2	0
97	Electrical spin injection in light emitting Schottky diodes based on InGaAs /GaAs QW heterostructures. AIP Conference Proceedings, 2007, , .	0.4	0
98	InGaAs/GaAs LIGHT-EMITTING DIODES WITH FERROMAGNETIC DELTA-DOPED LAYERS. , 2013, , .		0
99	The study of Si/Ge interdiffusion using molecular dynamics simulation. Journal of Physics: Conference Series, 2020, 1695, 012036.	0.4	0
100	Methods for Switching Radiation Polarization in GaAs Laser Diodes. Technical Physics, 2021, 66, 1194-1199.	0.7	0
101	Method for Forming Films of the Î²-FeSi2 Phase by Pulsed Laser Deposition in Vacuum. Semiconductors, 2021, 55, 749.	0.5	0
102	Formation of the diluted magnetic semiconductor phase by thermal diffusion in the pulsed laser deposition method. Journal of Physics: Conference Series, 2022, 2227, 012003.	0.4	0
103	Pulsed Laser Irradiation of Light-Emitting Structures with a (Ga,Mn)As Layer. Physics of the Solid State, 2021, 63, 1593-1600.	0.6	0